

Abstract of the Disclosure

In the single crystal SiC according to the invention, heat treatment is performed in an inert gas atmosphere under a state where a cutting plane of a single crystal α -SiC substrate which is produced in a plate-like form by cutting along (1 1 $\bar{2}$ 0) Miller index plane $\pm 10^\circ$, and (2 2 0) Miller index plane of a polycrystalline β -SiC plate are superimposed on each other, whereby single crystal having a crystal orientation of an orientation of the cutting plane is integrally grown in the polycrystalline β -SiC plate in conformity with the single crystal α -SiC substrate. According to this configuration, single crystal SiC of very high quality is obtained to which influence of micropipes of the single crystal α -SiC substrate is not transferred, thereby preventing distortion and micropipe defects from occurring.